

isc P-Channel MOSFET Transistor

2SJ126

DESCRIPTION

- Low Drain-Source ON Resistance
- High Forward Transfer Admittance
- Low Leakage Current
- Enhancement-Mode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

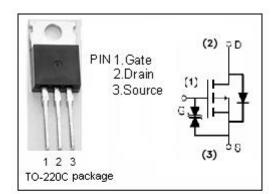
- High speed switching application
- Switching regulator ,DC-DC converter and Motor drive application

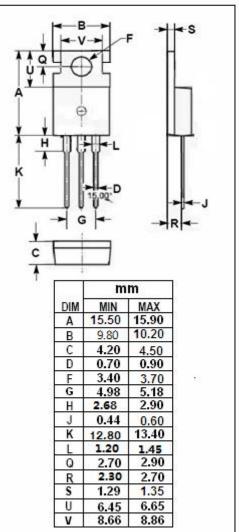
SYMBOL	ARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage (V _{GS} =0)	-60	V
V _{GS}	Gate-Source Voltage	±20	V
ID	Drain Current-continuous@ TC=37°C	-10	А
P _{tot}	Total Dissipation@TC=25°C	40	W
Tj	Max. Operating Junction Temperature	-55~150	°C
T _{stg}	Storage Temperature Range	-55~150	°C

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	3.1	°C/W
Rth j-a	Thermal Resistance, Junction to Ambient	75	°C/W







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ELECTRICAL CHARACTERISTICS (12-23 C)							
PARAMETER	CONDITIONS	MIN	МАХ	UNIT			
Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = -10mA	-60		V			
Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = -1mA	-1.5	-3.5	V			
Drain-Source On-stage Resistance	V _{GS} = -10V; I _D = -5A		0.4	Ω			
Gate Source Leakage Current	V _{GS} = -20V;V _{DS} = 0		-100	nA			
Zero Gate Voltage Drain Current	V _{DS} = -60V,V _{GS} = 0		-1	mA			
Diode Forward Voltage	I _F =-10 A;V _{GS} = 0		-4.5	V			
	PARAMETER Drain-Source Breakdown Voltage Gate Threshold Voltage Drain-Source On-stage Resistance Gate Source Leakage Current Zero Gate Voltage Drain Current	PARAMETERCONDITIONSDrain-Source Breakdown VoltageVGS = 0; ID = -10mAGate Threshold VoltageVDS = VGS; ID = -1mADrain-Source On-stage ResistanceVGS = -10V; ID = -5AGate Source Leakage CurrentVGS = -20V; VDS = 0Zero Gate Voltage Drain CurrentVDS = -60V, VGS = 0	PARAMETERCONDITIONSMINDrain-Source Breakdown VoltageVGS= 0; ID= -10mA-60Gate Threshold VoltageVDS= VGS; ID= -1mA-1.5Drain-Source On-stage ResistanceVGS= -10V; ID= -5A-1.5Gate Source Leakage CurrentVGS= -20V; VDS= 0-1.5Zero Gate Voltage Drain CurrentVDS= -60V, VGS= 0-1.5	PARAMETERCONDITIONSMINMAXDrain-Source Breakdown Voltage V_{GS} = 0; I_D = -10mA-60Gate Threshold Voltage V_{DS} = V_{GS} ; I_D = -1mA-1.5-3.5Drain-Source On-stage Resistance V_{GS} = -10V; I_D = -5A0.4Gate Source Leakage Current V_{GS} = -20V; V_{DS} = 0-100Zero Gate Voltage Drain Current V_{DS} = -60V, V_{GS} = 0-1			

• ELECTRICAL CHARACTERISTICS (Tc=25°C)

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